ABSTRACT OF THE DISCLOSURE

A photoelectric conversion device includes a photoelectric conversion layer that is stacked on a semiconductor substrate and that has first, second, and third photoelectric conversion regions, and first, second, and third dividing regions. The first dividing region is formed at a predetermined depth from a surface of the photoelectric conversion layer in the first photoelectric conversion region, and divides the first photoelectric conversion region into a first surface side region closer to the surface thereof and a first substrate side region closer to the semiconductor substrate. The first dividing region has a through hole. The second dividing region is formed at substantially the same depth as the first dividing region or at a shallower depth than the first dividing region in the second photoelectric conversion region. The third dividing region is formed at a shallower depth than the second dividing region in the third photoelectric conversion region.